



TECHNICAL DATA SHEET

DATA SHEET NO. 1003A

August 1988

High Voltage Power MOSFET Die

N-Channel Enhancement Mode High Ruggedness Series

The following device types use the IRFC350:

2N6768
2N6767
IRF350/IRFP350
IRF351/IRFP351
IRF352/IRFP352
IRF353/IRFP353

FEATURES:

- Fast switching times
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Excellent high voltage stability
- Low input capacitance
- Improved high temperature reliability

APPLICATIONS:

- Switching power supplies
- Motor controls
- Audio Amplifiers
- Inverters
- Choppers

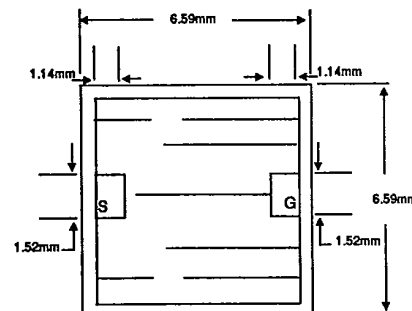
IRFC350

$V_{(BR)DSS}$ 400V
 $R_{DS(on)}$ 0.3 Ω

Die Topography

Notes:

1. Top Metal 3 μ m Aluminum
2. Back Metal Ni/V, with Au
3. Die thickness 420 $\pm$ 10 μ m



ELECTRICAL CHARACTERISTICS: (TA=25 °C unless otherwise specified)

CHARACTERISTIC	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	$V_{(BR)DSS}$	400	—	—	V
Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	$V_{GS(th)}$	2.0	—	4.0	V
Gate-Source Leakage Current	$V_{GS} = \pm 20 \text{ V}_{DC}$	I_{GSS}	—	—	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = V_{(BR)DSS} \times 0.8$, $V_{GS} = 0 \text{ V}$ $T_C = 25^\circ\text{C}$ $T_C = 125^\circ\text{C}$	I_{DSS}	—	—	250	μA
		I_{DSS}	—	—	1000	μA
Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 8.0 \text{ A}$	$R_{DS(ON)}$	—	—	0.3	Ω
Ciss Input Capacitance	$V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1.0 \text{ MHz}$	Ciss	—	—	3000	pF
Coss Output Capacitance	Pulse Test: Pulse width $\leq 300 \text{ ms}$, duty cycle $\leq 2\%$	Coss	—	—	500	pF
Crss Reverse Transfer Capacitance		Crss	—	—	200	pF

NOTES:

1. I_D based on $R_{thJC} = 0.83^\circ\text{C/W}$
2. ASSEMBLY RECOMMENDATIONS:
 - a) 10 mil Gate and 15 mil Source wires
 - b) Drain mounted with 92.5/5/2.5% Lead/Indium/Silver solder, or 95/5% Lead/tin solder
3. Devices shipped in ESD protected waffle packs with a maximum of 25 die per waffle pack.
4. Die should be handled and assembled in clean room environment.
5. Die should be stored in inert atmosphere (1 atmosphere N_2)

IXYS Corporation reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Corporation

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